

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	2Ω @ V <sub>GS</sub> = 10V	356mA
	3Ω @ V <sub>GS</sub> = 5V	294mA

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor controls
- Power-management functions

## Features and Benefits

- Low On-Resistance: R<sub>DS(ON)</sub>
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN601LTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

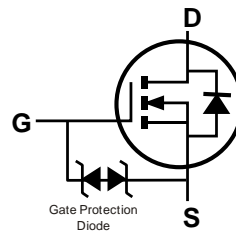
- Package: SOT523
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



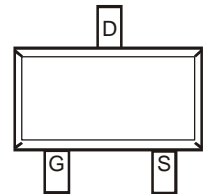
SOT523



Top View



Equivalent Circuit



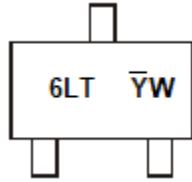
Top View  
Pin Out Configuration

## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN601LTQ-7	SOT523	3,000	Tape & Reel
DMN601LTQ-13	SOT523	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



6LT = Product Type Marking Code  
 YW = Date Code Marking  
 Y = Year (ex: 3 = 2023)  
 W = Week (ex: a = week 27; z represents week 52 and 53)

### Date Code Key

Year	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	3	4	5	6	7	8	9	0	1	2	3	4

Week	1-26	27-52	53
Code	A-Z	a-z	z

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	I <sub>D</sub>	Steady State	356	mA
		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	285	
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	356	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	1.2	A	

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	0.4	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	298	°C/W
Total Power Dissipation (Note 5)	P <sub>D</sub>	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	242	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.0 1.1	2 3	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 200mA V <sub>GS</sub> = 5V, I <sub>D</sub> = 150mA
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	47	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	5.3	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	4.7	—	pF	
Gate Resistance	R <sub>g</sub>	—	140	—	Ω	f = 1MHz, V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	0.7	—	nC	V <sub>DS</sub> = 15V I <sub>D</sub> = 200mA
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	1.3	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.3	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.1	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V R <sub>g</sub> = 150Ω, I <sub>D</sub> = 200mA
Turn-On Rise Time	t <sub>r</sub>	—	11.4	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	48.5	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	21.2	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	18.6	—	ns	I <sub>F</sub> = 1A, dI/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	7.7	—	nC	I <sub>F</sub> = 1A, dI/dt = 100A/μs

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

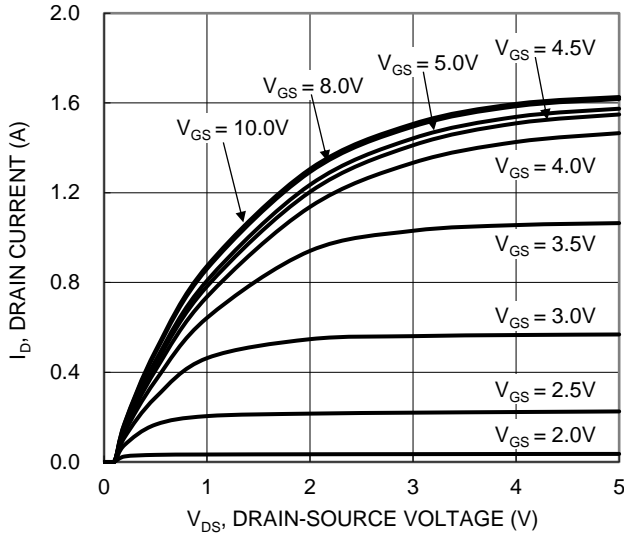


Figure 1. Typical Output Characteristic

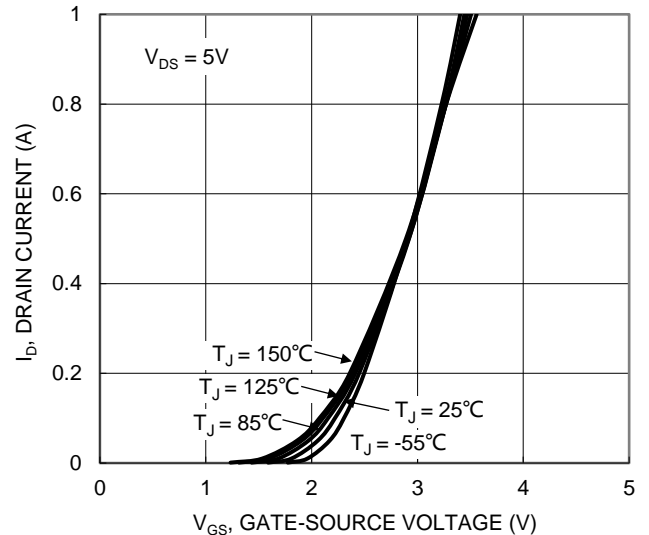


Figure 2. Typical Transfer Characteristic

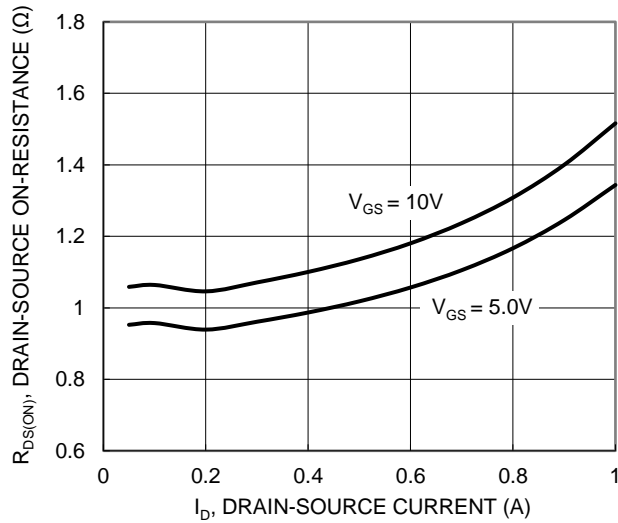


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

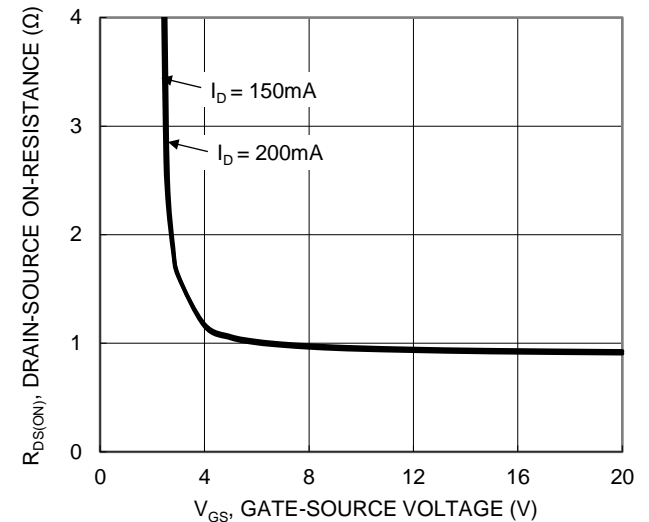


Figure 4. Typical Transfer Characteristic

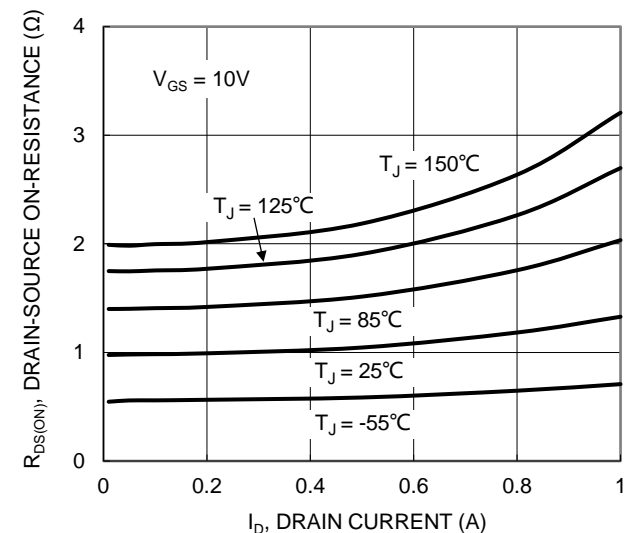


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

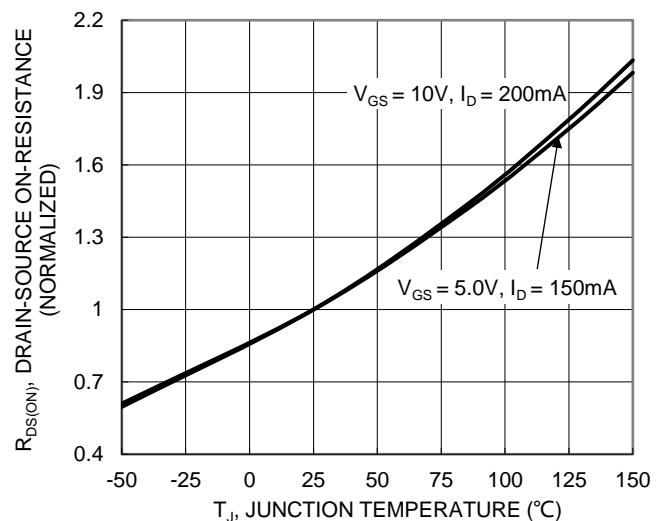


Figure 6. On-Resistance Variation with Junction Temperature

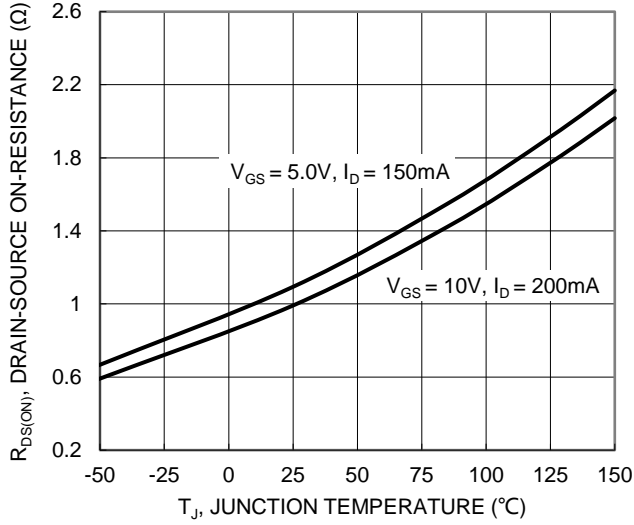


Figure 7. On-Resistance Variation with Junction Temperature

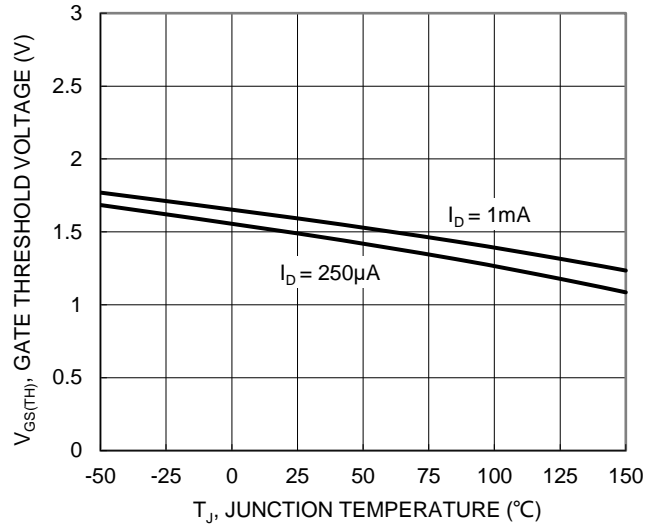


Figure 8. Gate Threshold Variation vs. Junction Temperature

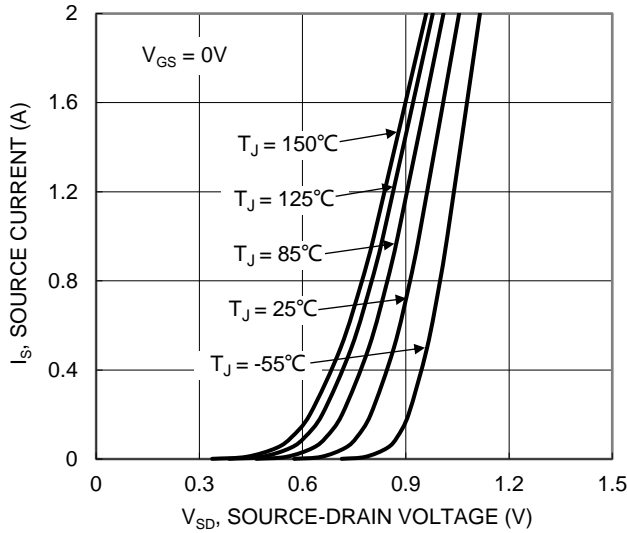


Figure 9. Diode Forward Voltage vs. Current

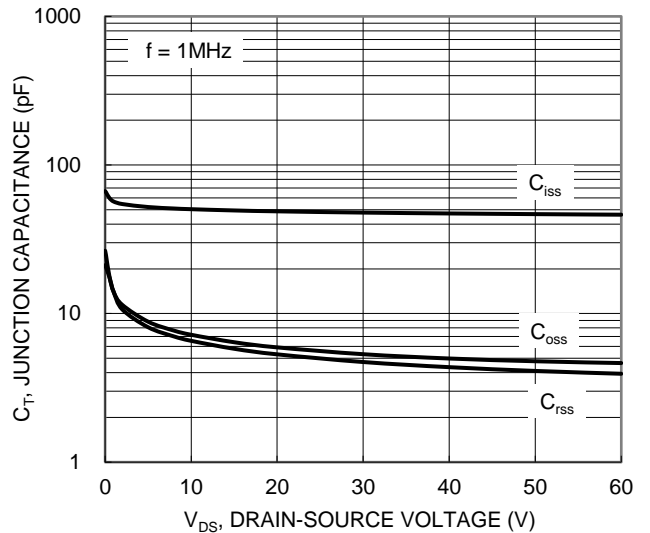


Figure 10. Typical Junction Capacitance

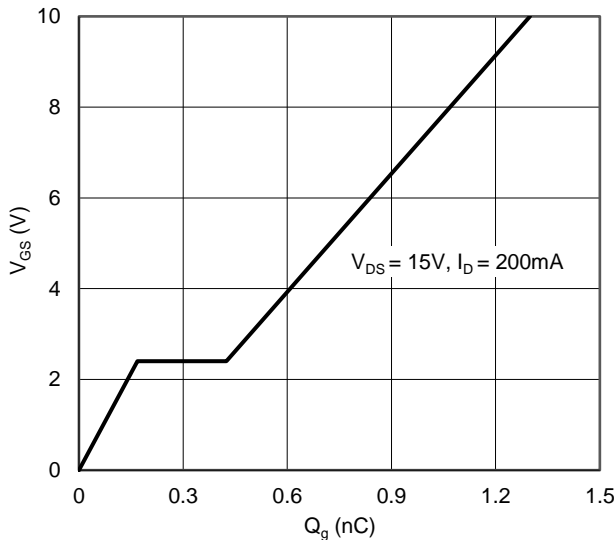


Figure 11. Gate Charge

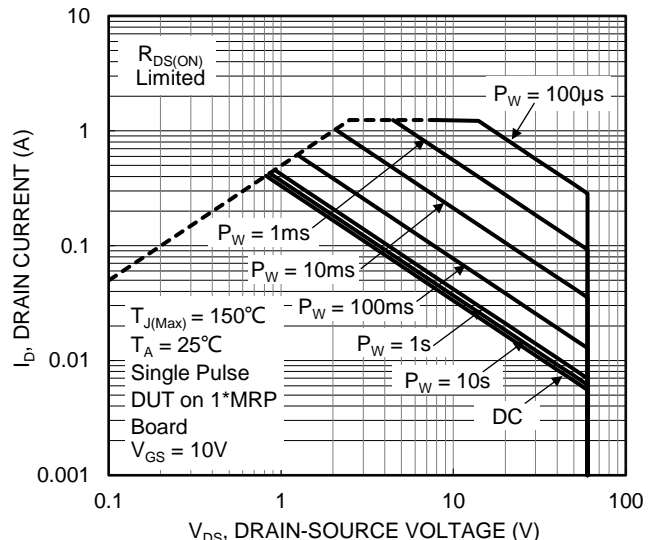


Figure 12. SOA, Safe Operation Area

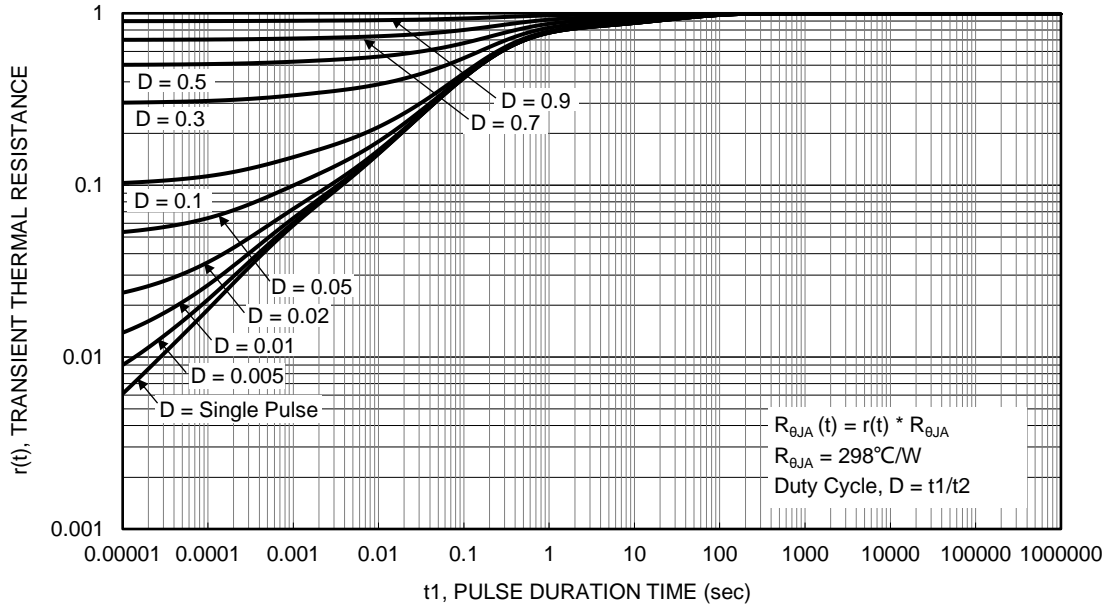
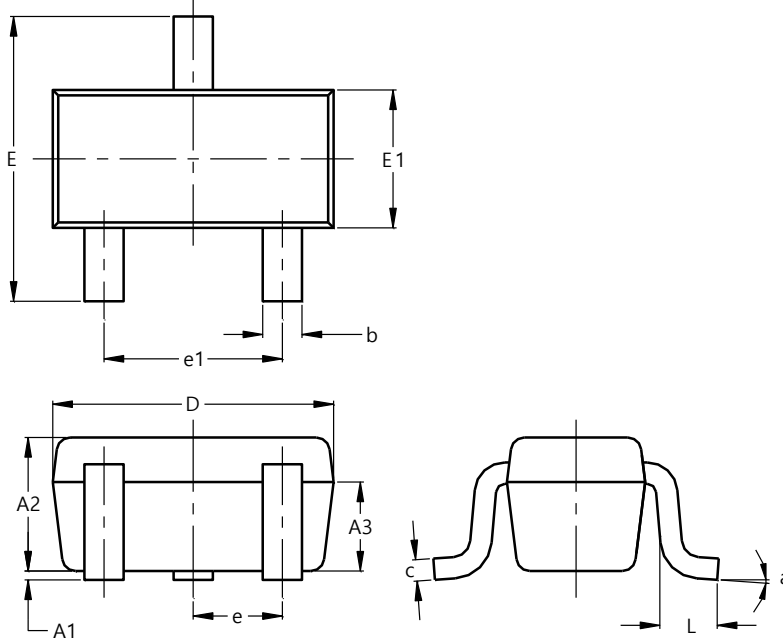


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**

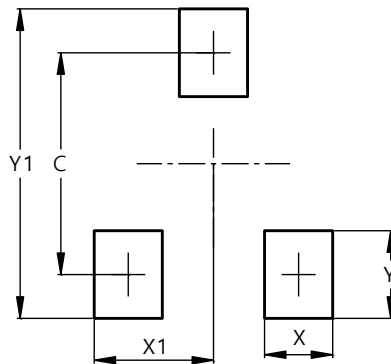


SOT523			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**



Dimensions	Value (in mm)
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80

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